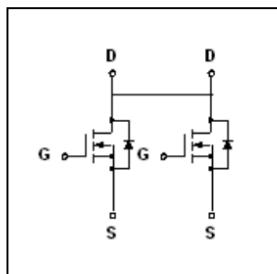


Dual N-Channel Power MOSFET

FEATURES

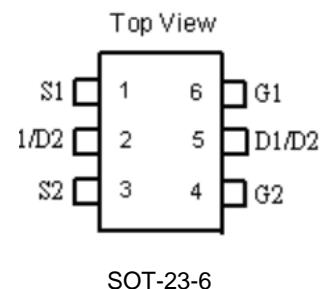
- 20V 5A N-channel Trench Mosfet
- RDSON \leqslant 27m Ω @Vgs=4.5V, Id=5A
- RDSON \leqslant 36m Ω @Vgs=2.5V, Id=3A
- Low gate Charge
- Fast switching capability
- High reliability and rugged

SYMBOL



APPLICATION

- Portable Equipment
- Battery Powered System



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	± 12	V
Drain Current(Note1)	Continuous	I _D	A
	Pulsed	I _{DM}	A
Power Dissipation (TA=25°C) (Note 2)	TA=25°C	P _D	0.83
	TA=100°C		0.3
Thermal Resistance-Junction to Ambient	R _{θJA}	150	°C/W
Maximum Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to 150	°C

Note: 1. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%

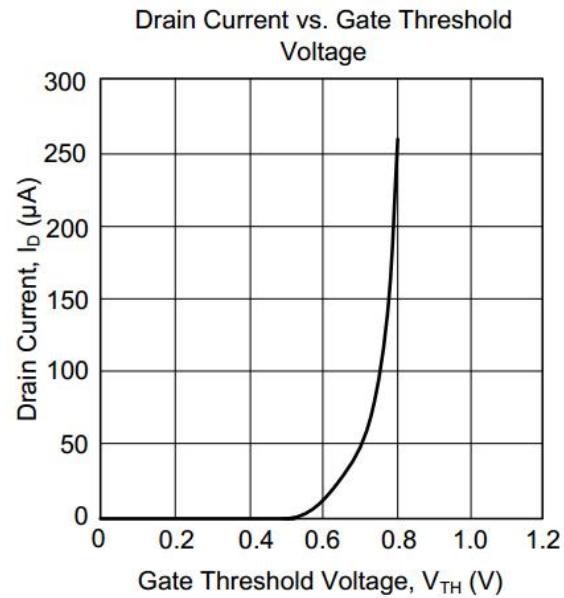
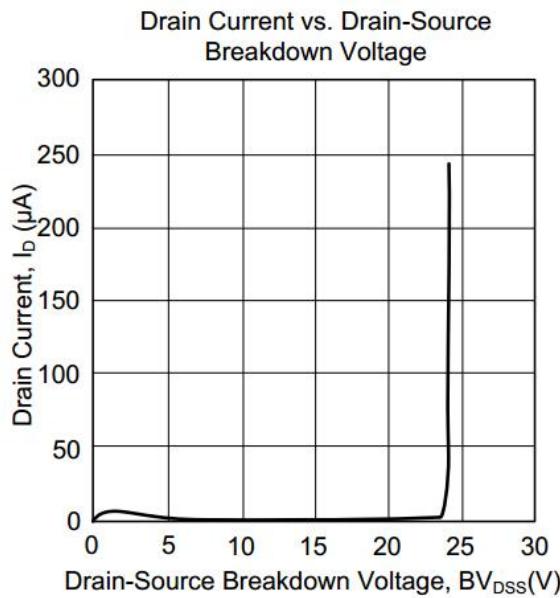
2. Pulse width limited by T_J(MAX)

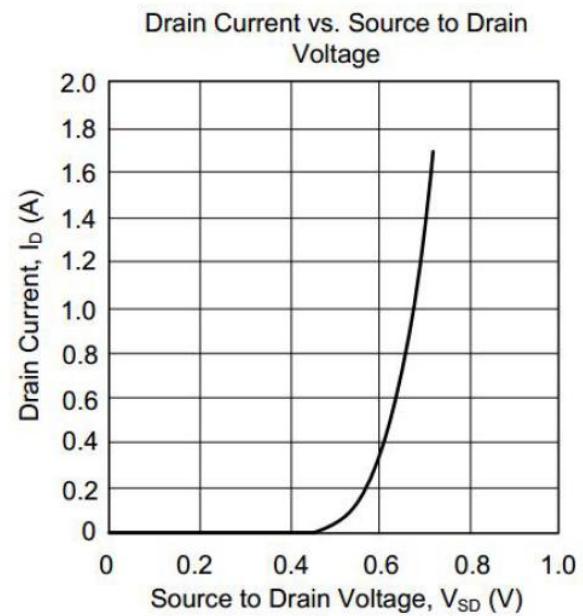
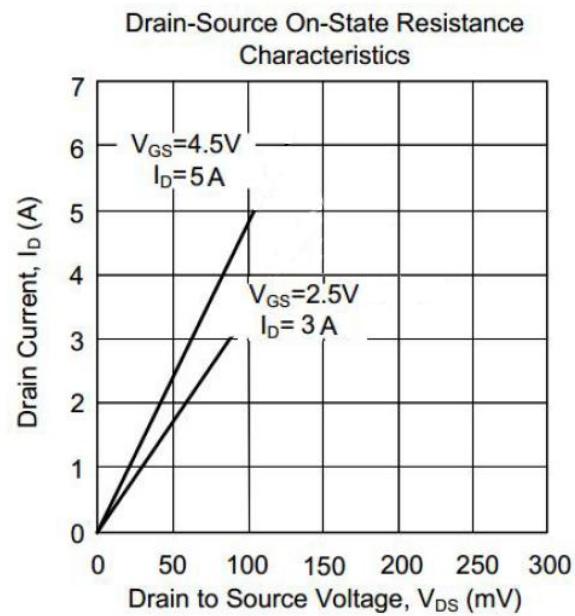
ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, ID=250 μ A	20			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = \pm 8V			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , ID=250 μ A	0.5		1.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, ID=5.0A		22	27	m Ω
		V _{GS} =2.5V, ID=3A		28	36	m Ω

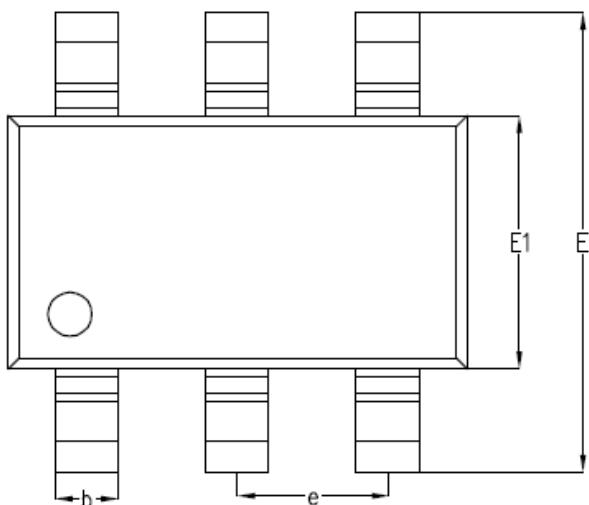
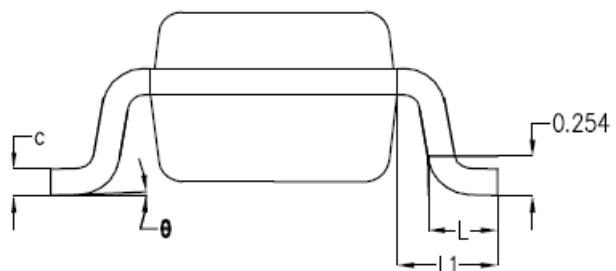
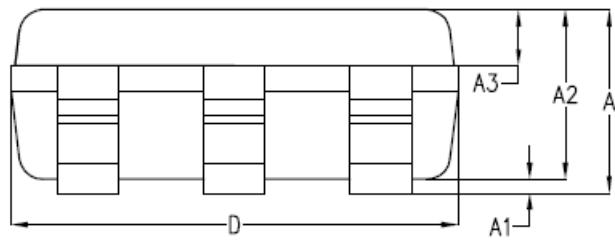
ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	VDS=10V, VGS=0V, f=1.0MHz		630		pF
Output Capacitance	C _{OSS}			312		pF
Reverse Transfer Capacitance	C _{RSS}			145		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time (Note)	t _{D(ON)}	VGS=4V, VDS=10V, RD=10Ω, RG=10Ω, ID=1A		18		ns
Turn-ON Rise Time	t _R			5		ns
Turn-OFF Delay Time	t _{D(OFF)}			42		ns
Turn-OFF Fall-Time	t _F			19		ns
Total Gate Charge(Note)	Q _G	VDS =20V, VGS =5V, ID =5.0A		23		nC
Gate Source Charge	Q _{GS}			4.5		nC
Gate Drain Charge	Q _{GD}			6.8		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	IS=1.7A, VGS=0V		1.2		V
Diode Continuous Forward Current	I _S	VD=VG, VS=1.3V		1.5		A

TYPICAL CHARACTERISTICS



SOT-23-6 Package Information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	-	1.19	1.24
A1	-	0.05	0.09
A2	1.05	1.10	1.15
A3	0.31	0.36	0.41
b	0.35	0.40	0.45
c	0.12	0.17	0.22
D	2.85	2.90	2.95
E	2.80	2.90	3.00
E1	1.55	1.60	1.65
e	0.95BSC		
L	0.37	0.45	0.53
L1	0.65BSC		
θ	0°	2°	8°

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